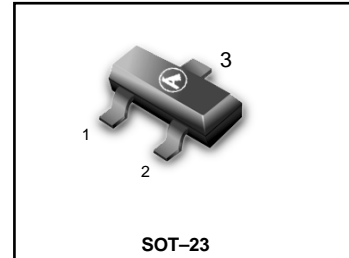


Monolithic Dual Switching Diode

LBAV74LT1G
S-LBAV74LT1G

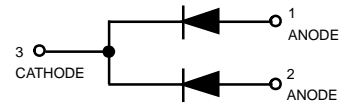
Features

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



ORDERING INFORMATION

Device	Marking	Shipping
LBAV74LT1G S-LBAV74LT1G	JA	3000/Tape&Reel
LBAV74LT3G S-LBAV74LT3G	JA	10000/Tape&Reel



MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	50	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Reverse Breakdown Voltage ($I_{(BR)} = 5.0 \mu\text{Adc}$)	$V_{(BR)}$	50	—	Vdc
Reverse Voltage Leakage Current ($V_R = 50 \text{ Vdc}$, $T_J = 125^\circ\text{C}$) ($V_R = 50 \text{ Vdc}$)	I_R	—	100 0.1	μAdc
Diode Capacitance ($V_R = 0$, $f = 1.0 \text{ MHz}$)	C_D	—	2.0	pF
Forward Voltage ($I_F = 100 \text{ mAdc}$)	V_F	—	1.0	Vdc
Reverse Recovery Time ($I_F = 10 \text{ mAdc}$, $I_{R(REC)} = 1.0 \text{ mAdc}$, measured at $I_R = 1.0 \text{ mA}$, $R_L = 100\Omega$)	t_{rr}	—	4.0	ns

1. FR-5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$

2. Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.

LBAV74LT1G,S-LBAV74LT1G

Curves Applicable to Each Anode

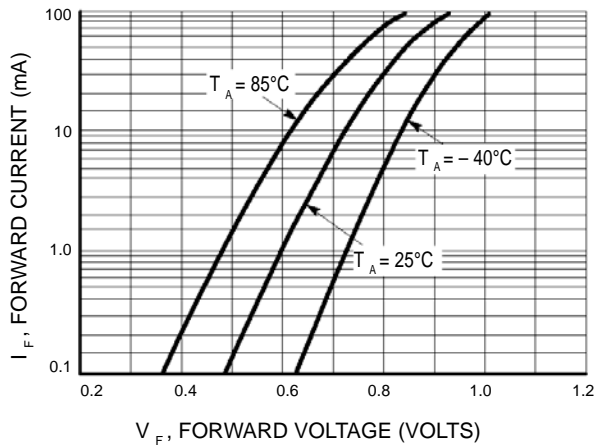


Figure 1. Forward Voltage

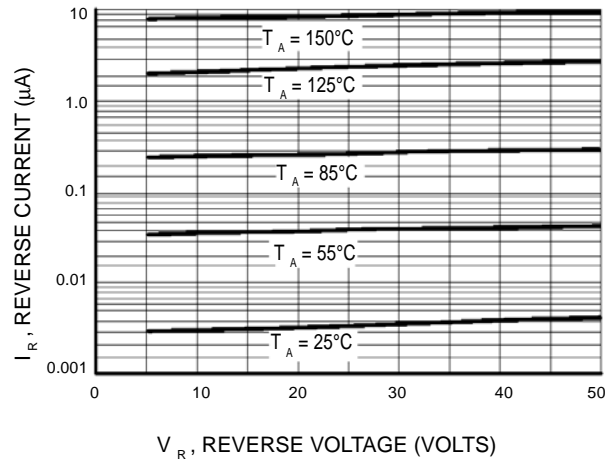


Figure 3. Leakage Current

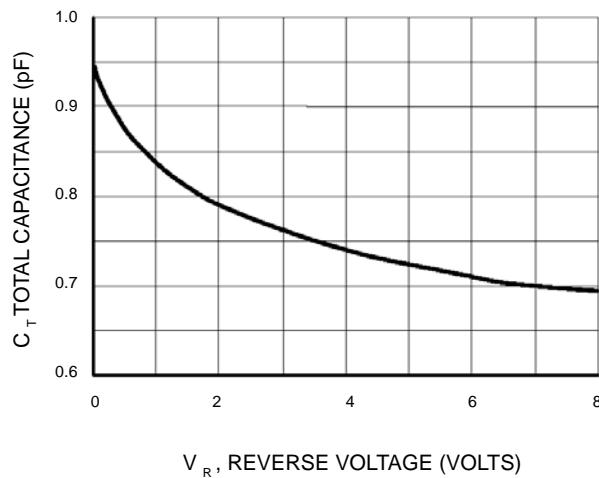
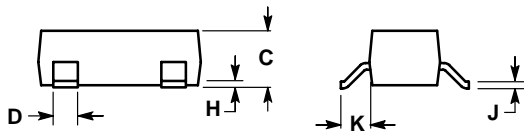
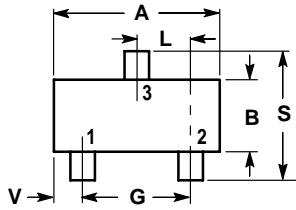


Figure 3. Capacitance

LBAV74LT1G,S-LBAV74LT1G

SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. ANODE
 2. NO CONNECTION
 3. CATHODE

